

## **Surface Mount UES Rectifiers**

**PRODUCT PREVIEW** 

#### **DESCRIPTION**

This state of the art high frequency rectifier is ideally suited for applications requiring high blocking voltage. It has the ability to switch significant current with minimal switching transients and losses. Leakage current at high temperature has been minimized;

achieving exceptionally low reverse loses. An ultra stable process ensures high reliability and long life.

This device is designed for a wide variety of high-frequency applications.

## **KEY FEATURES**

- Ultra Fast Recovery-35ns
- Controlled Avalanche
- High Temperature Operation with Low Loss
- Minimal Recovery Transients
- Low Turn-on Voltage
- Powermite 3 Package

IMPORTANT: For the most current data, consult MICROSEMP's website: http://www.microsemi.com

#### **ABSOLUTE MAXIMUM RATINGS AT 25° C** (UNLESS OTHERWISE SPECIFIED) Rating **Symbol** Value Unit V Peak Reverse Voltage UPR802 200 $V_{R1}$ Peak Reverse Voltage UPR804 $V_{R1}$ 400 ٧ Peak Reverse Voltage UPR806 $V_{R1}$ 600 V Average DC Output Current Tc = 130 °C Ιo 8 Α Peak Forward Surge Current 8.3 mS $V_{\rm F}$ 100 Α Storage Temperature ٥С T stg -55 to 150 Operating Temperature Тор -55 to 150 ٥С

## APPLICATIONS/BENEFITS

- Battery Charger and Switching Circuits Where the intrinsic source-drain diode is an undesirable feature
- Small foot print



>	THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED)				
Ī	Thermal Resistance				
	Junction-to Case	Rjtab	2.0	°C/Watt	

- (1) Mounted on 2" square by 0.06' thick FR4 board with a 1" x 1" square 2 ounce copper pattern.
- (2) Mounted on 0.06 thick FR4 board, using recommended footprint.



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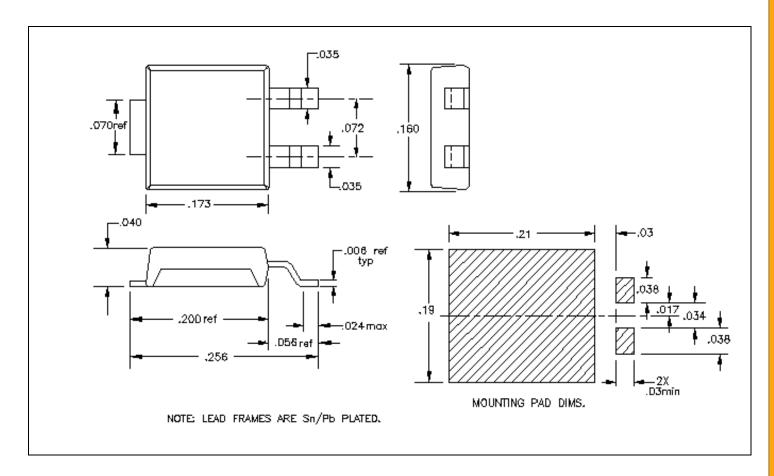
Parameter	Symbol	Conditions	Тур.	Units	
<ul> <li>On characteristics (pulsed Width = 400 μs, Duty Cycle &lt;1%)</li> </ul>					
Forward Voltage	Vf	I <sub>F</sub> = 4.0A	1.2	V	
Forward Voltage	Vf	I <sub>F</sub> = 8.0A	1.35	V	
Forward Voltage Tc = 125 °C	Vf	$I_F = 8.0A$	1.1	V	
Reverse Current	$I_R$	$Ir = V_R$	10	μΑ	
Reverse Current Tc = 125 °C	$I_R$	$Ir = V_R$	250	μΑ	
► Switching characteristics (Tc = 25 °C)					
Reverse Recovery Time	TIRM/ IRM	dI/dt = 100 A/μs	35	ns	

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